



**Ordering Information:**

**Absolute Maximum Ratings  $T_c = 25$**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	80	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V

$I_{D@TC=25}$

Continuous Drain Current

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	2.8	$^{\circ}C/W$
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	$^{\circ}C$

**Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	80	85		V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.3		2.3	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 80V, V_{GS} = 0V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance		$V_{GS} = 10V, I_D = 40A$				
Forward Transconductance	$g_{FS}$	$V_{DS} = 10V, I_D = 20A$				

**Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	$C_{iss}$	$f = 1MHz$	-	3300	-	pF
Output capacitance	$C_{oss}$		-	260	-	
Reverse transfer capacitance	$C_{rss}$		-	170	-	

**Gate Charge characteristics( $T_a = 25$  )**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	$Q_g$	$V_{DD} = 25V$	-	65	-	nC
Gate - Source charge	$Q_{gs}$	$I_D = 8A$	-	13		
		$V_{GS} = 10V$				



Fig.1 Power Dissipation Derating Curve

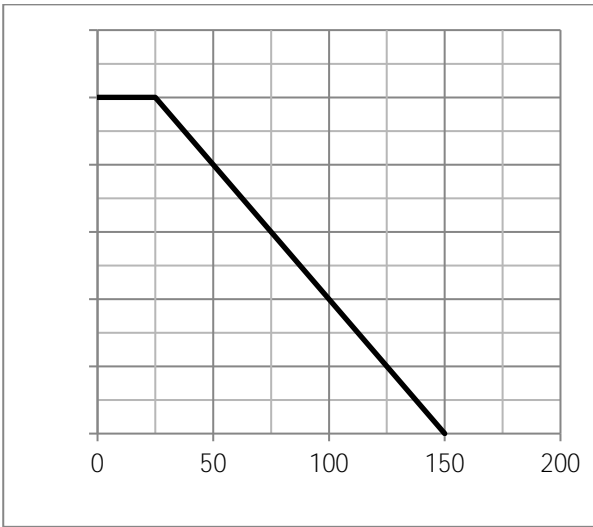


Fig.2 Typical output Characteristics

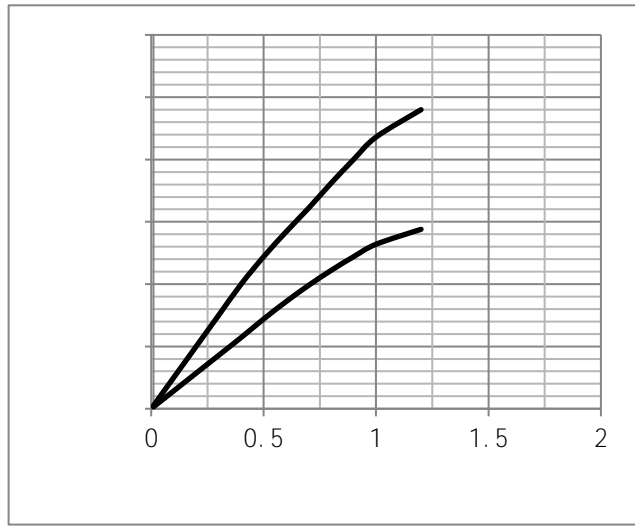


Fig.3 Threshold Voltage V.S Junction Temperature

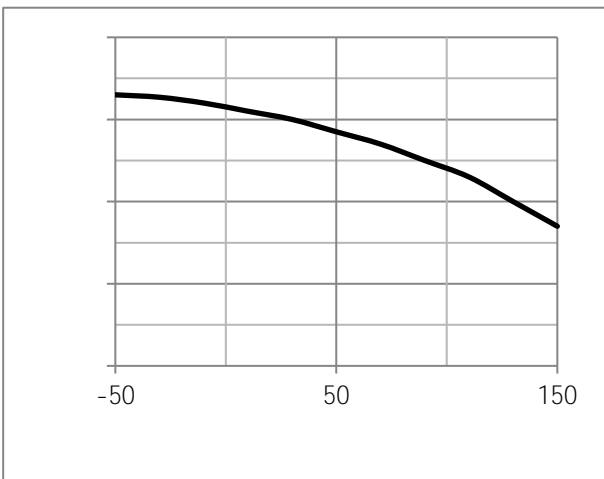


Fig.4 Resistance V.S Drain Current

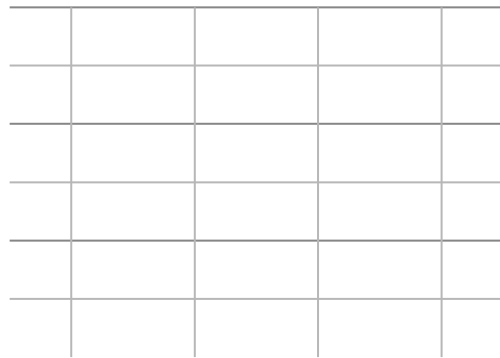




Fig.7 Switching Time Measurement Circuit

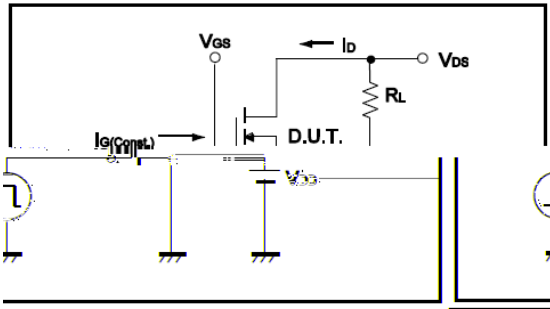


Fig.8 Gate Charge Waveform

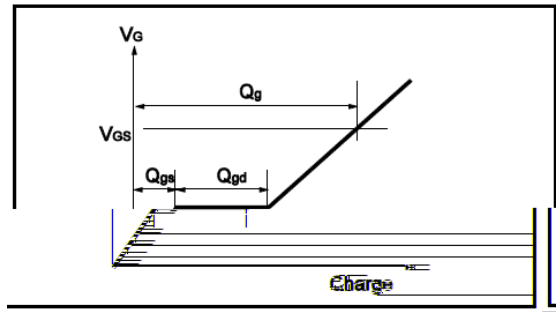


Fig.9 Switching Time Measurement Circuit

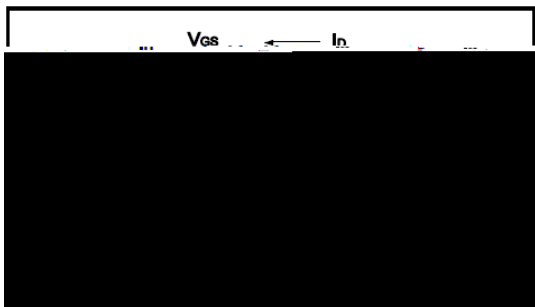


Fig.10 Gate Charge Waveform

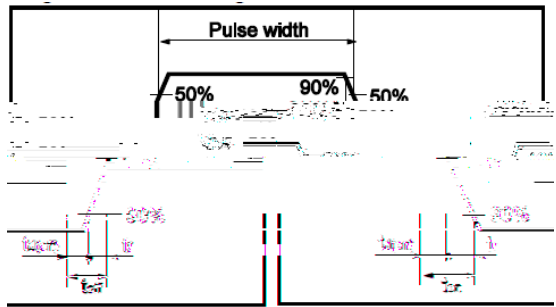


Fig.11 Avalanche Measurement Circuit

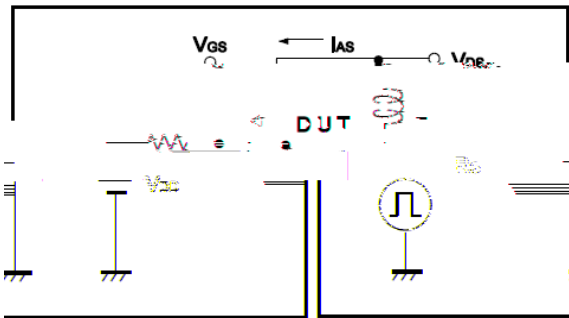


Fig.12 Avalanche Waveform

